

Preparation of Titania Solid Films by Laser CVD using CO₂ Laser

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Abstract. Titania (TiO₂) films having dense and solid microstructure were prepared by laser chemical vapor deposition using CO₂ laser. The effects of deposition temperature (T_{dep}) and total chamber pressure (P_{tot}) on phase and microstructure of TiO₂ films were investigated. At $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 790$ K, rutile TiO₂ film had a polygonal platelet grains 2 μm in size. At $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 1010$ K, rutile TiO₂ film had (110) orientation and consisted of a truncated polyhedron 5–6 μm in size. At $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 955$ K, rutile TiO₂ film has a solid columnar having faceted surface. A dense and solid TiO₂ film was obtained at $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 1120$ K. The deposition rate of TiO₂ solid film was reached 240 $\mu\text{m h}^{-1}$.

Introduction

Titania (TiO₂) has attracted much attention as protective and optical coatings because of their high resistance to chemical and physical impact, low thermal conductivity, high refractive index and photoinduced catalysis and superhydrophilicity [1,2]. Thick TiO₂ films having dense and solid microstructure are suitable as protective coatings. Physical vapor deposition technique, such as sputtering, pulsed laser deposition and electron-beam evaporation, can prepare a dense and smooth film; however, its deposition rate is usually too low (several hundred nanometers per hour) for industrial applications. Thermal spraying can be an alternative thick coating technique, but disadvantages of this method are a porous structure and microcracking in the film.

Chemical vapor deposition (CVD), including thermal CVD, metalorganic CVD and plasma-enhanced CVD, has been widely used for preparing protective coatings with excellent step coverage and a relatively high deposition rate; however, the deposition rates less than several micrometers per hour are still insufficient for thick coatings. We have employed laser CVD to prepare Y₂O₃-ZrO₂ and Al₂O₃ films at high deposition rates (up to 500–600 $\mu\text{m h}^{-1}$) [3,4]. Laser CVD can also prepare dense SiO₂ thick films at a significant high deposition rate of 1200 $\mu\text{m h}^{-1}$ [5]. Laser irradiation to the deposition zone during the CVD process can enhance the chemical reactions of the precursor gas and accelerate the surface mobility of adsorbed species on the film surface.

In the present study, TiO₂ films having dense and solid microstructure were prepared by laser CVD using CO₂ laser.

Experimental procedure

A schematic of laser CVD apparatus has been reported elsewhere [6]. Ti(OiPr)₂(dpm)₂ (titanium diisopropoxy-dipivaloylmethanate) precursor was heated at 453 K and its vapor were carried into the chamber with Ar gas (gas flow rate: 0.17 Pa m³ s⁻¹). O₂ gas was separately introduced into the chamber through a double-tube nozzle (gas flow rate: 0.17 Pa m³ s⁻¹). Precursor gas line and double-tube nozzle were heated at 453 and 473 K, respectively, to prevent condensation of the precursor during transportation. The total pressure in the chamber was held at 200 and 600 Pa. Yttria-stabilized zirconia (YSZ) plate (8 mm × 8 mm × 1 mm) was used as a substrate. The substrate was heated on a hot stage at a preheating temperature of 873 K, and a thermocouple was inserted backside of the substrate to measure the deposition temperature (T_{dep}). A CO₂ laser beam (Synrad

firestar f200; wavelength: 10.6 μm) was introduced through a quartz window to irradiate the whole substrate. Deposition was conducted for 600 s.

The crystal phase was analyzed by X-ray diffraction (XRD, Rigaku RAD-2C) using $\text{Cu K}\alpha$ X-ray radiation. The surface and cross-sectional morphology was observed by a scanning electron microscope (SEM, Hitachi S-3100H). A schematic of crystal structure was illustrated by VESTA, a three-dimensional visualization system [7].

Results and discussion

Figure 1 shows the XRD patterns of TiO_2 films prepared at P_{tot} and T_{dep} . At $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 930$ K, XRD patterns can be indexed as rutile TiO_2 having (110) orientation (space group: $P4_2/mnm$; lattice parameters: $a = 0.459$ nm, $c = 0.296$ nm) with a minor amount of anatase TiO_2 ($I4_1/amd$; $a = 0.378$ nm, $c = 0.951$ nm) (Fig. 1(a)). At T_{dep} greater than 865 K, single-phase rutile TiO_2 films were obtained (Fig. 1(b)), while the (110) orientation degree slightly decreased with increasing T_{dep} . At $P_{\text{tot}} = 200$ Pa, XRD patterns of TiO_2 films can be indexed as rutile TiO_2 irrespective of T_{dep} . Rutile TiO_2 film prepared at $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 1120$ K showed a significant (110) orientation (Fig. 1(c)).

Ramamoorthy *et al.* calculated surface energies of (110), (100), (001) and (011) surface of rutile TiO_2 using first-principles calculations [8]. Figure 2 shows the equilibrium shape of a rutile TiO_2 crystal illustrated by Wulff construction with the surface energies. Surface energy of (110), (100), (011) and (001) surface were 15.6, 19.6, 24.4 and 28.9 meV a.u.^{-2} , respectively. According to the calculations, (110) surface has the lowest energy, implying a significant (110)-orientation growth of rutile TiO_2 films.

Figure 3 shows the surface and cross-sectional SEM images of rutile TiO_2 films prepared at various P_{tot} and T_{dep} . TiO_2 film had polygonal platelet grains 2 μm in size at $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 790$ K (Fig. 3(a)). As shown in Fig. 2, the platelet facet may be (110) surface. At $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 1010$ K, TiO_2 film consisted of a truncated polyhedron 5–6 μm in

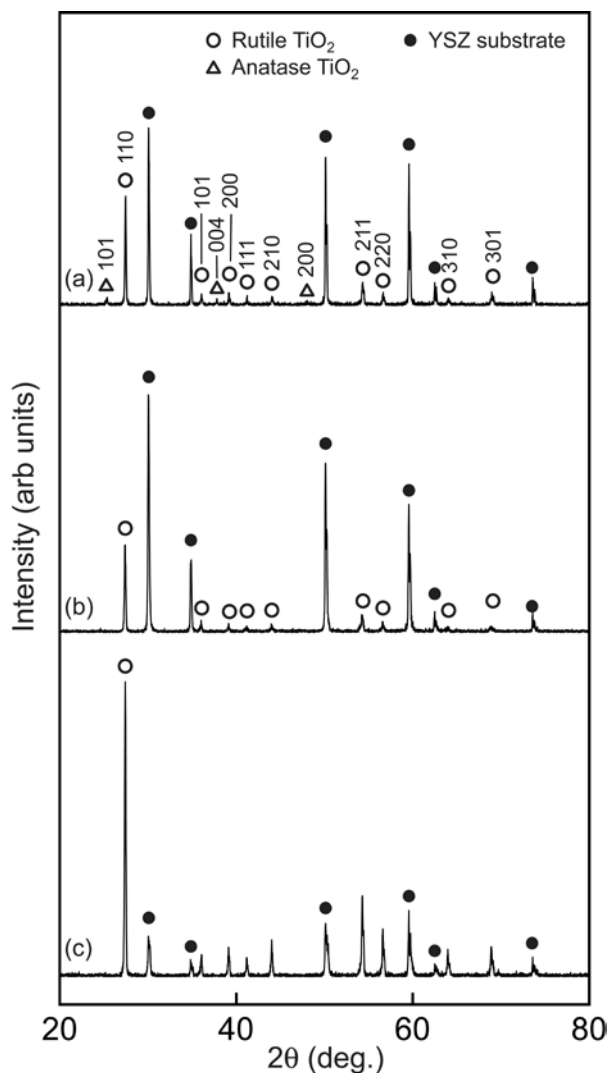


Fig. 1 XRD patterns of the TiO_2 films prepared various P_{tot} and T_{dep} : 600 Pa and 790 K (a), 600 Pa and 1010 K (b), and 200 Pa and 1120 K (c).

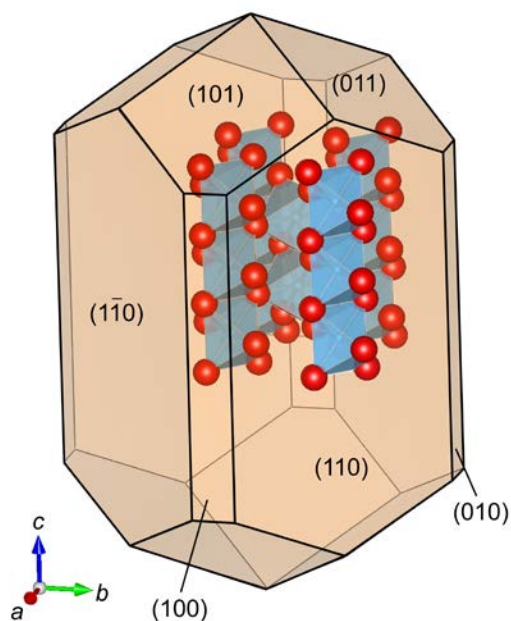


Fig. 2 The equilibrium shape of a rutile TiO_2 crystal based on surface energies.

size (Fig. 3(b)). This truncated polyhedral shape might also be explained by the equilibrium shape of rutile TiO_2 . TiO_2 film has a solid columnar having faceted surface at $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 955$ K (Fig. 3(c), 3(c')). At $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 1120$ K, a dense and solid TiO_2 film was obtained (Fig. 3(d), 3(d')). Deposition rates of the TiO_2 films were ranged from 120 to 240 $\mu\text{m h}^{-1}$.

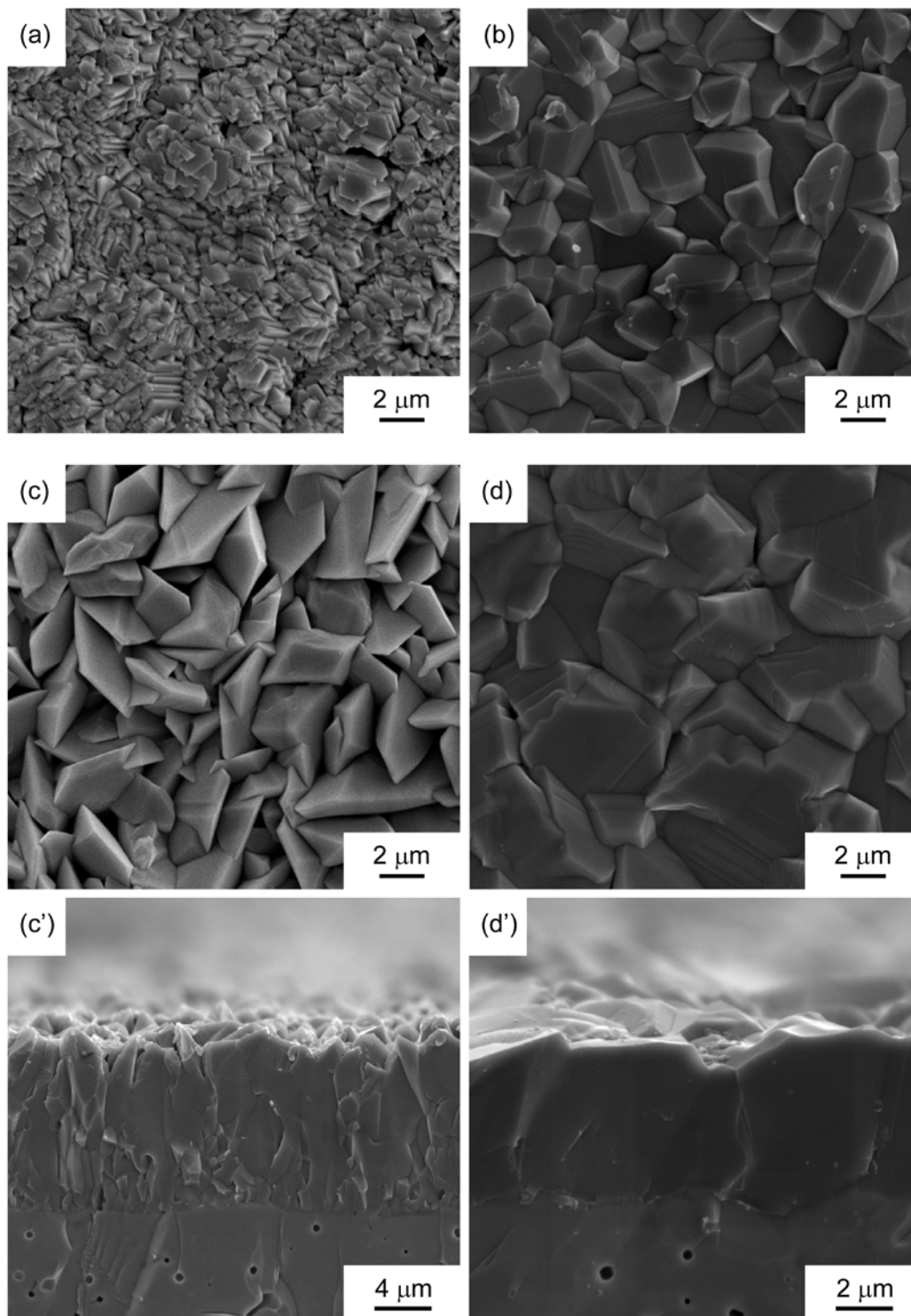


Fig. 2 Surface (a-d) and cross-sectional (c', d') SEM images of TiO_2 films prepared at various P_{tot} and T_{dep} : 600 Pa and 790 K (a), 600 Pa and 1010 K (b), 200 Pa and 955 K (c), and 200 Pa and 1120 K (d).

Summary

Rutile TiO₂ films having dense and solid microstructure were prepared by laser CVD using CO₂ laser. At $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 790$ K, rutile TiO₂ film had polygonal platelet grains 2 μm in size. At $P_{\text{tot}} = 600$ Pa and $T_{\text{dep}} = 1010$ K, rutile TiO₂ film had (110) orientation and consisted of a truncated polyhedron 5–6 μm in size. At $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 955$ K, rutile TiO₂ film has a solid columnar having faceted surface. A dense and solid TiO₂ film was obtained at $P_{\text{tot}} = 200$ Pa and $T_{\text{dep}} = 1120$ K. Faceted microstructure of the rutile TiO₂ films can be associated with the equilibrium shape of a rutile TiO₂. The deposition rate of TiO₂ solid film was reached 240 μm h⁻¹.

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